TOSHIBA

MICROWAVE SEMICONDUCTOR
TECHNICAL DATA

MICROWAVE POWER MMIC AMPLIFIER TMD1925-3

FEATURES

n HIGH POWER

P1dB=35.0dBm at 1.9GHz to 2.5GHz

n HIGH GAIN

G1dB=29.0dB at 1.9GHz to 2.5GHz

n Broad Band Internally Matched

n HERMETICALLY SEALED PACKAGE

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-4
Input Power	Pin	dBm	13
Flange Temperature	Tf	°C	-30 ~ +80
Storage Temperature	T _{stg}	°C	-65 ~ + 175

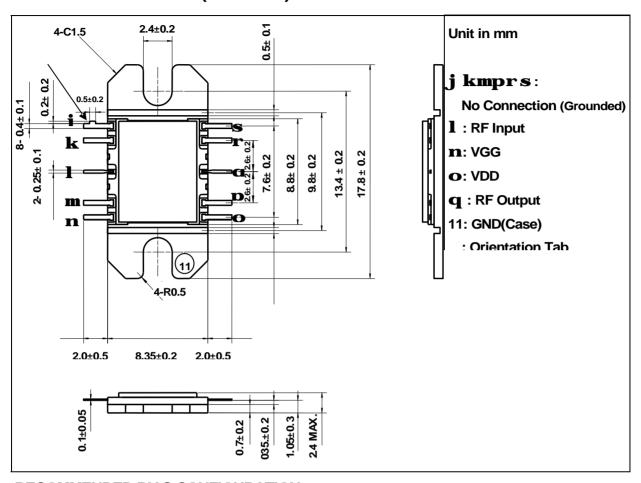
RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Operating Frequency	f		GHz	1.9		2.5
Output Power at 1dB Gain	P1dB		dBm	34.0	35.0	
Compression Point						
Power Gain at 1dB Gain	G1dB	VDD= 10V	dB	27.0	29.0	
Compression Point		IDDset=1.2A				
Gain Flatness	ΔG		dB			±1.5
Drain Current	IDD		Α		1.6	1.9

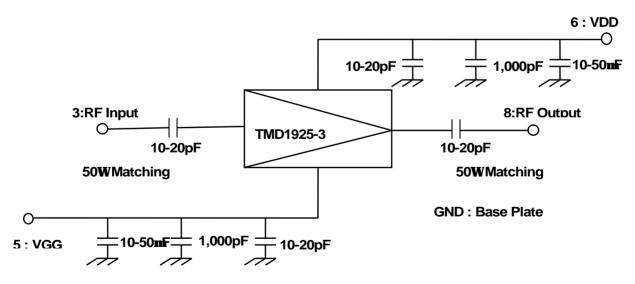
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PACKAGE OUTLINE (7-BA06A)



RECOMMENDED BIAS CONFIGURATION



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.